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[International Rectifier \(Infineon Technologies Americas Corp.\)](#)
[IRLMS4502TR](#)

For any questions, you can email us directly:

sales@integrated-circuit.com

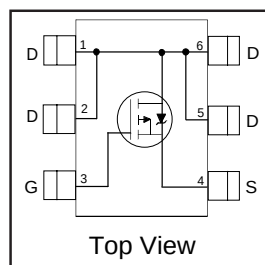
International IOR Rectifier

PD- 93759B

IRLMS4502

HEXFET® Power MOSFET

- Ultra Low On-Resistance
- P-Channel MOSFET
- Surface Mount
- Available in Tape & Reel



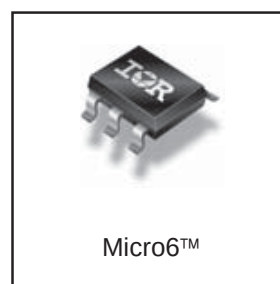
$$V_{DSS} = -12V$$

$$R_{DS(on)} = 0.042\Omega$$

Description

These P-Channel MOSFETs from International Rectifier utilize advanced processing techniques to achieve the extremely low on-resistance per silicon area. This benefit provides the designer with an extremely efficient device for use in battery and load management applications..

The Micro6 package with its customized leadframe produces a HEXFET power MOSFET with $R_{DS(on)}$ 60% less than a similar size SOT-23. This package is ideal for applications where printed circuit board space is at a premium. It's unique thermal design and $R_{DS(on)}$ reduction enables a current-handling increase of nearly 300% compared to the SOT-23.



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain- Source Voltage	-12	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	-5.5	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	-4.4	
I_{DM}	Pulsed Drain Current ①	-44	
$P_D @ T_A = 25^\circ C$	Power Dissipation	1.7	W
$P_D @ T_A = 70^\circ C$	Power Dissipation	1.1	
	Linear Derating Factor	0.013	W/°C
E_{AS}	Single Pulse Avalanche Energy④	28	mJ
V_{GS}	Gate-to-Source Voltage	± 12	V
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

	Parameter	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient③	75	°C/W

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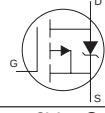
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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	-12	—	—	V	V _{GS} = 0V, I _D = -250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	-0.003	—	V/°C	Reference to 25°C, I _D = -1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	0.042	Ω	V _{GS} = -4.5V, I _D = -5.5A ②
		—	—	0.075		V _{GS} = -2.5V, I _D = -4.7A ②
V _{GS(th)}	Gate Threshold Voltage	-0.60	—	—	V	V _{DS} = V _{GS} , I _D = -250μA
g _{fs}	Forward Transconductance	8.8	—	—	S	V _{DS} = -10V, I _D = -5.5A
I _{DSS}	Drain-to-Source Leakage Current	—	—	-1.0	μA	V _{DS} = -12V, V _{GS} = 0V
		—	—	-25		V _{DS} = -9.6V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	V _{GS} = -12V
	Gate-to-Source Reverse Leakage	—	—	100		V _{GS} = 12V
Q _g	Total Gate Charge	—	22	33	nC	I _D = -5.5A
Q _{gs}	Gate-to-Source Charge	—	3.9	5.8		V _{DS} = -10V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	11	16		V _{GS} = -5.0V ②
t _{d(on)}	Turn-On Delay Time	—	18	—	ns	V _{DD} = -6.0V
t _r	Rise Time	—	460	—		I _D = -1.0A
t _{d(off)}	Turn-Off Delay Time	—	130	—		R _G = 4.5Ω
t _f	Fall Time	—	250	—		R _D = 6.0Ω ②
C _{iss}	Input Capacitance	—	1820	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	1110	—		V _{DS} = -10V
C _{rss}	Reverse Transfer Capacitance	—	1070	—		f = 1.0kHz

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	-1.7	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	-44		
V _{SD}	Diode Forward Voltage	—	—	-1.2	V	T _J = 25°C, I _S = -1.7A, V _{GS} = 0V ③
t _{rr}	Reverse Recovery Time	—	31	46	ns	T _J = 25°C, I _F = -5.5A
Q _{rr}	Reverse Recovery Charge	—	21	32	nC	di/dt = -100A/μs ②

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Pulse width ≤ 400μs; duty cycle ≤ 2%.
- ③ Surface mounted on FR-4 board, t ≤ 5sec.
- ④ Starting T_J = 25°C, L = 1.8mH
R_G = 25Ω, I_{AS} = -5.5A. (See Figure 12)

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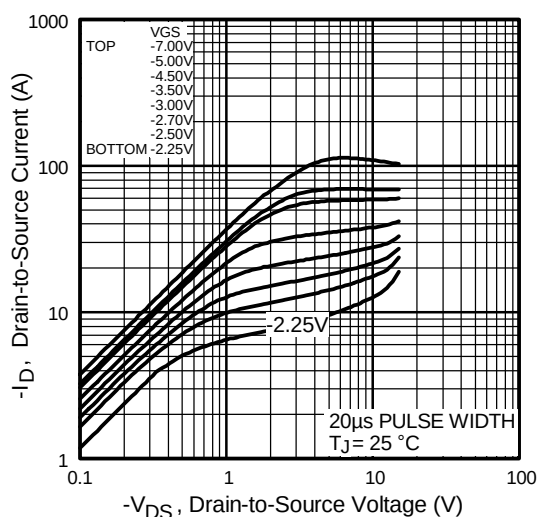


Fig 1. Typical Output Characteristics

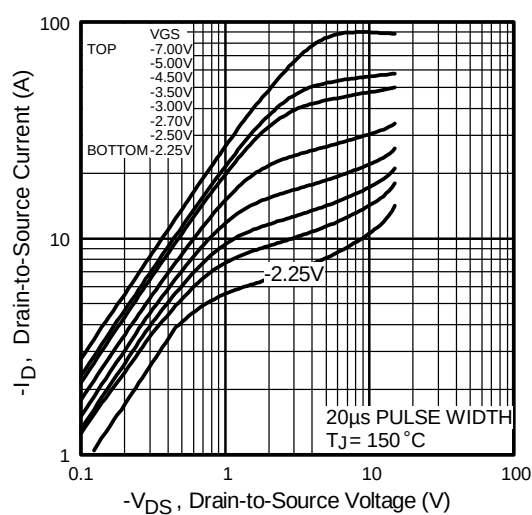


Fig 2. Typical Output Characteristics

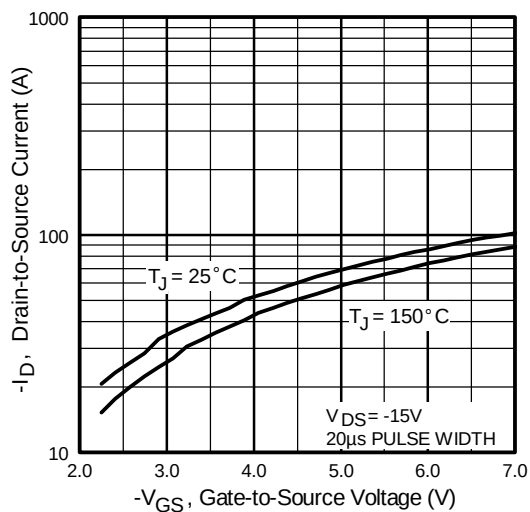


Fig 3. Typical Transfer Characteristics

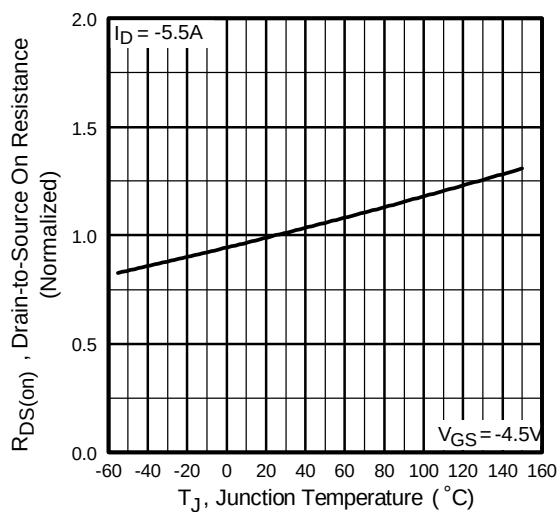


Fig 4. Normalized On-Resistance Vs. Temperature

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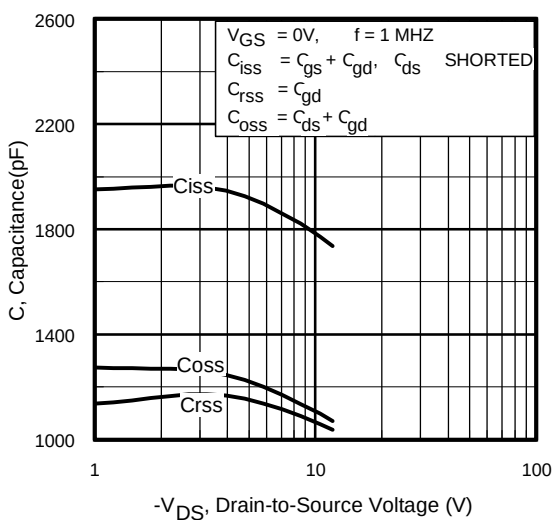


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

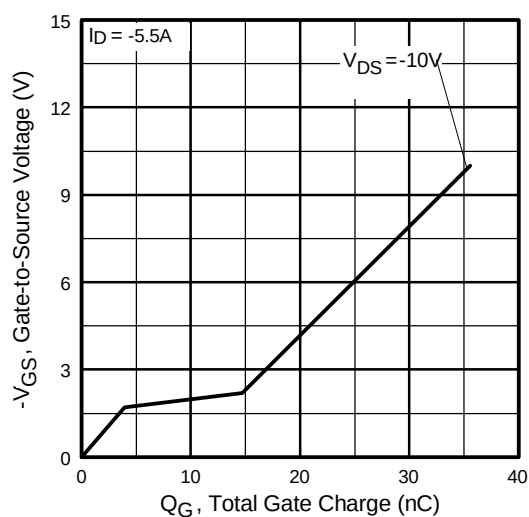


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

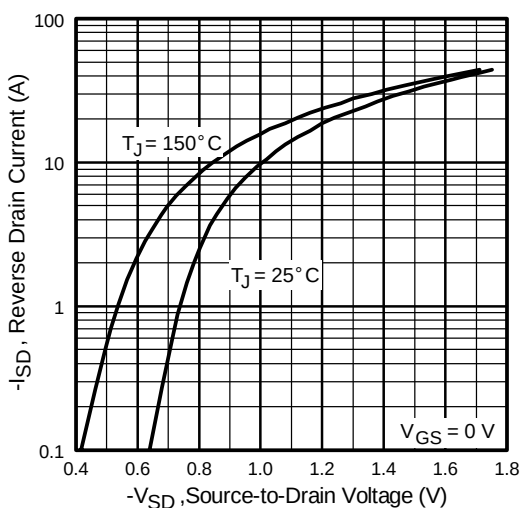


Fig 7. Typical Source-Drain Diode Forward Voltage

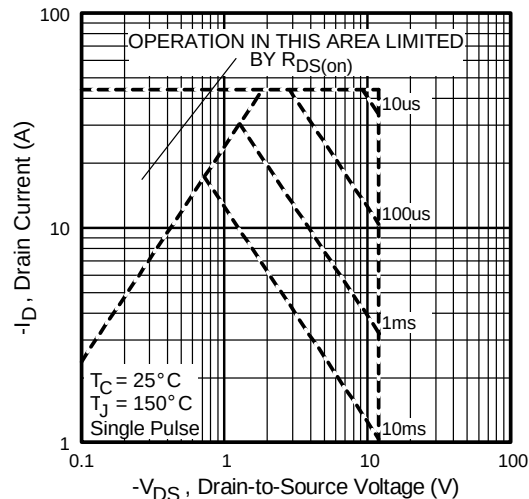


Fig 8. Maximum Safe Operating Area

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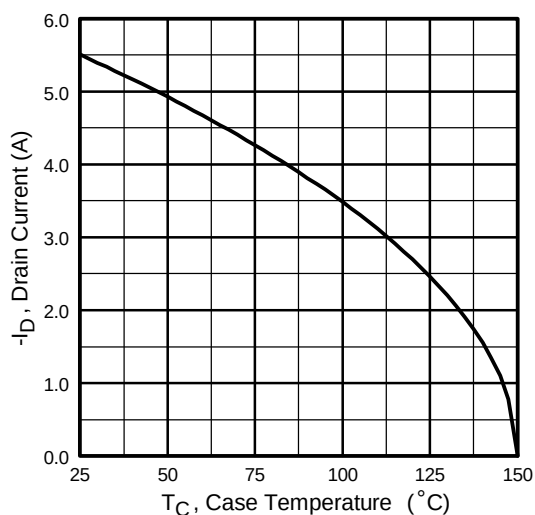


Fig 9. Maximum Drain Current Vs. Case Temperature

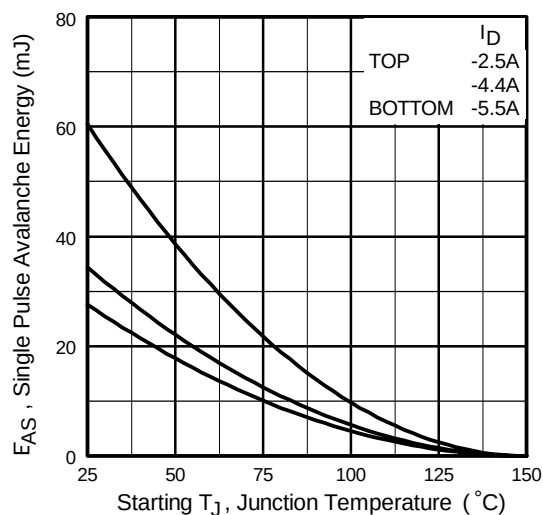


Fig 10. Maximum Avalanche Energy Vs. Drain Current

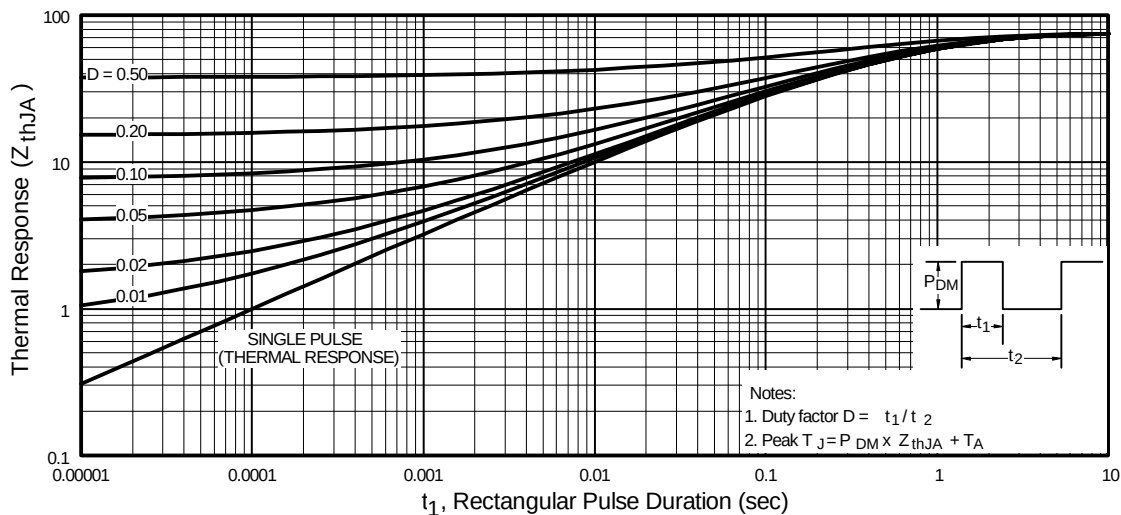
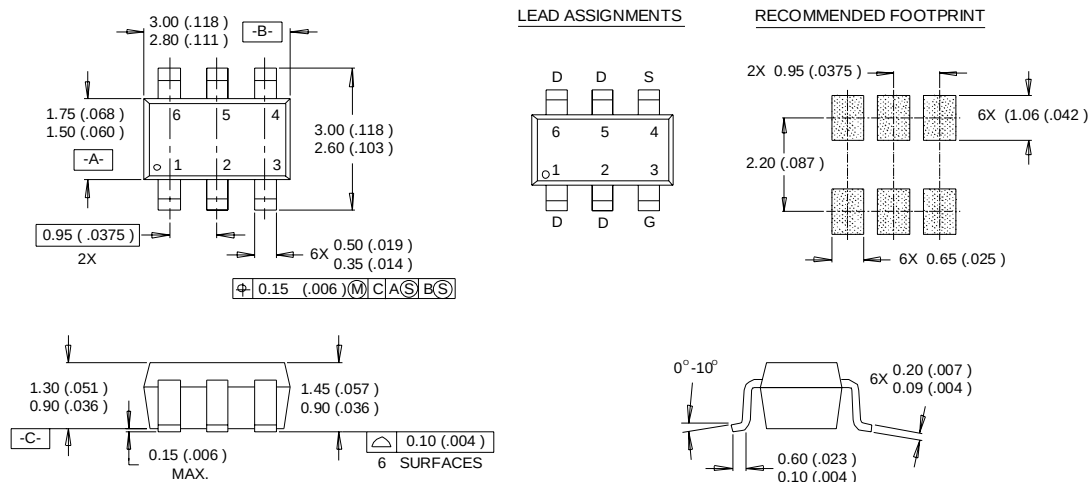


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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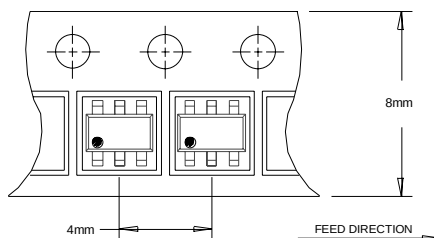
Micro6™ Package Outline



NOTES :

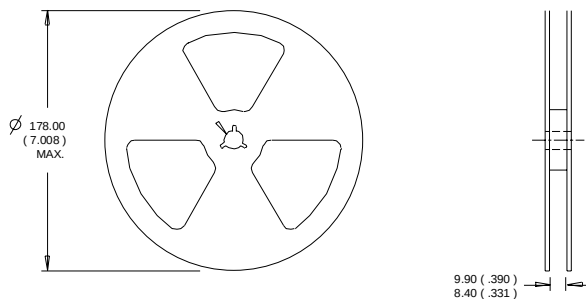
1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982.
2. CONTROLLING DIMENSION : MILLIMETER.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).

Micro6™ Tape & Reel Information



NOTES :

1. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES:

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

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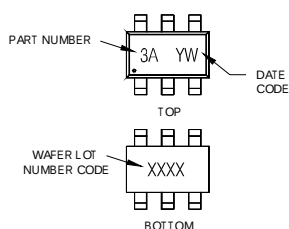
Micro6™ Part Marking Information

IRLMS4502

Notes: This part marking information applies to devices produced before 02/26/2001

EXAMPLE: THIS IS AN IRLMS6702

WW = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR



PART NUMBER CODE REFERENCE:

2A = IRLMS1902
2B = IRLMS1503
2C = IRLMS6702
2D = IRLMS5703
2E = IRLMS6802
2F = IRLMS4502
2G = IRLMS2002
2H = IRLMS6803

DATE CODE EXAMPLES:

YWW = 9603 = 6C
YWW = 9632 = FF

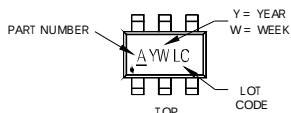
YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
2004	4	04	D
2005	5		
1996	6		
1997	7		
1998	8		
1999	9		
2000	0	24	X
		25	Y
		26	Z

WW = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
2004	D	30	D
2005	E		
1996	F		
1997	G		
1998	H		
1999	J		
2000	K	50	X
		51	Y
		52	Z

Notes: This part marking information applies to devices produced after 02/26/2001

W = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR



PART NUMBER CODE REFERENCE:

A = IRLMS1902
B = IRLMS1503
C = IRLMS6702
D = IRLMS5703
E = IRLMS6802
F = IRLMS4502
G = IRLMS2002
H = IRLMS6803

YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
2004	4	04	D
2005	5		
1996	6		
1997	7		
1998	8		
1999	9		
2000	0	24	X
		25	Y
		26	Z

W = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
2004	D	30	D
2005	E		
1996	F		
1997	G		
1998	H		
1999	J		
2000	K	50	X
		51	Y
		52	Z

This product has been designed and qualified for the consumer market.
Qualification Standards can be found on IR's Web site.

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Data and specifications subject to change without notice. 01/03

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